

MEDIUM POWER THYRISTORS

Stud Version

Features

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High di/dt and dv/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1600V V_{DRM}/V_{RRM}

22A

Typical Applications

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high-reliability requirements

Major Ratings and Characteristics

Parameters	22RIA		Units
	10 to 120	140 to 160	
$I_{T(AV)}$	22	22	A
@ T_C	85	85	°C
$I_{T(RMS)}$	35	35	A
I_{TSM}	@50Hz	340	A
	@60Hz	355	A
I^2t	@50Hz	575	A ² s
	@60Hz	525	A ² s
V_{DRM}/V_{RRM}	100 to 1200	1400 to 1600	V
t_q	typical	110	µs
T_J	- 65 to 125		°C



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage (1) V	V_{RSM} , maximum non-repetitive peak voltage (2) V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA
22RIA	10	100	150	10
	20	200	300	
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	
	140	1400	1500	
	160	1600	1700	

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dI/dt does not exceed 20A/ μ s(2) For voltage pulses with $t_p \leq 5$ ms

On-state Conduction

Parameter	22RIA		Units	Conditions
	10 to 120	140 to 160		
$I_{T(AV)}$ Max. average on-state current @ Case temperature	22	22	A	180° sinusoidal conduction
	85	85	°C	
$I_{T(RMS)}$ Max. RMS on-state current	35	35	A	
I_{TSM} Max. peak, one-cycle non-repetitive surge current	400	340	A	t = 10ms No voltage t = 8.3ms reapplied
	420	355		t = 10ms 100% V_{RRM} t = 8.3ms reapplied
	335	285		Sinusoidal half wave, Initial $T_J = T_J$ max.
	355	300		
I^2t Maximum I^2t for fusing	793	575	A ² s	t = 10ms No voltage t = 8.3ms reapplied
	724	525		t = 10ms 100% V_{RRM} t = 8.3ms reapplied
	560	405		
	515	370		
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	7930	5750	A ² \sqrt{s}	t = 0.1 to 10ms, no voltage reapplied, $T_J = T_J$ max.
$V_{T(TO)1}$ Low level value of threshold voltage	0.83	1.01	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	0.95	1.17		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	14.9	12.24	m Ω	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t2} High level value of on-state slope resistance	13.4	10.35		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
V_{TM} Max. on-state voltage	1.70	—	V	$I_{pk} = 70$ A, $T_J = 25^\circ\text{C}$
	—	1.80		
I_H Maximum holding current	130		mA	$T_J = 25^\circ\text{C}$. Anode supply 6V, resistive load,
I_L Latching current	200			

Switching

Parameter	22RIA	Units	Conditions
di/dt Max. rate of rise of turned-on current $V_{DRM} \leq 600V$ $V_{DRM} \leq 800V$ $V_{DRM} \leq 1000V$ $V_{DRM} \leq 1600V$	200 180 160 150	A/ μs	$T_J = T_J \text{ max.}, V_{DM} = \text{rated } V_{DRM}$ Gate pulse = 20V, 15 Ω , $t_p = 6\mu s$, $t_r = 0.1\mu s \text{ max.}$ $I_{TM} = (2x \text{ rated } di/dt) A$
t_{gt} Typical turn-on time	0.9		$T_J = 25^\circ C,$ at = rated V_{DRM}/V_{RRM} , $T_J = 125^\circ C$
t_{rr} Typical reverse recovery time	4	μs	$T_J = T_J \text{ max.},$ $I_{TM} = I_{T(AV)}, t_p > 200\mu s, di/dt = -10A/\mu s$
t_q Typical turn-off time	110		$T_J = T_J \text{ max.}, I_{TM} = I_{T(AV)}, t_p > 200\mu s, V_R = 100V,$ $di/dt = -10A/\mu s, dv/dt = 20V/\mu s \text{ linear to}$ $67\% V_{DRM}$, gate bias 0V-100W

(*) $t_q = 10\mu s$ up to 600V, $t_q = 30\mu s$ up to 1600V available on special request.

Blocking

Parameter	22RIA	Units	Conditions
dv/dt Max. critical rate of rise of off-state voltage	100	V/ μs	$T_J = T_J \text{ max. linear to } 100\% \text{ rated } V_{DRM}$
	300 (*)		$T_J = T_J \text{ max. linear to } 67\% \text{ rated } V_{DRM}$

(**) Available with: $dv/dt = 1000V/\mu s$, to complete code add S90 i.e. 22RIA160S90.

Triggering

Parameter	22RIA	Units	Conditions
P_{GM} Maximum peak gate power	8.0	W	$T_J = T_J \text{ max.}$
$P_{G(AV)}$ Maximum average gate power	2.0		
I_{GM} Max. peak positive gate current	1.5	A	$T_J = T_J \text{ max.}$
$-V_{GM}$ Maximum peak negative gate voltage	10	V	$T_J = T_J \text{ max.}$
I_{GT} DC gate current required to trigger	90	mA	$T_J = -65^\circ C$
	60		$T_J = 25^\circ C$
	35		$T_J = 125^\circ C$
V_{GT} DC gate voltage required to trigger	3.0	V	$T_J = -65^\circ C$
	2.0		$T_J = 25^\circ C$
	1.0		$T_J = 125^\circ C$
I_{GD} DC gate current not to trigger	2.0	mA	$T_J = T_J \text{ max.}, V_{DRM} = \text{rated value}$
V_{GD} DC gate voltage not to trigger	0.2	V	$T_J = T_J \text{ max.}$ $V_{DRM} = \text{rated value}$ Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied

22RIA Series

Bulletin I2403 rev. A 07/00

International
IRF Rectifier

Thermal and Mechanical Specification

Parameter	22RIA	Units	Conditions	
T _J Max. operating temperature range	- 65 to 125	°C		
T _{stg} Max. storage temperature range	- 65 to 125	°C		
R _{thJC} Max. thermal resistance, junction to case	0.86	K/W	DC operation	
R _{thCS} Max. thermal resistance, case to heatsink	0.35	K/W	Mounting surface, smooth, flat and greased	
T Mounting torque	to nut	to device	Lubricated threads (Non-lubricated threads)	
	20(27.5)	25		lbf-in
	0.23(0.32)	0.29		kgf.m
	2.3(3.1)	2.8		Nm
wt Approximate weight	14 (0.49)	g (oz)		
Case style	TO-208AA (TO-48)		See Outline Table	

ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.21	0.15	K/W	T _J = T _J max.
120°	0.25	0.25		
90°	0.31	0.34		
60°	0.45	0.47		
30°	0.76	0.76		

Ordering Information Table

Device Code	22	RIA	160	M	S90
	1	2	3	4	5
1	- Current code				
2	- Essential part number				
3	- Voltage code: Code x 10 = V _{RRM} (See Voltage Rating Table)				
4	- None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A M = Stud base TO-208AA (TO-48) M6 X 1				
5	- Critical dv/dt: None = 300V/μs (Standard value) S90 = 1000V/μs (Special selection)				

Outline Table

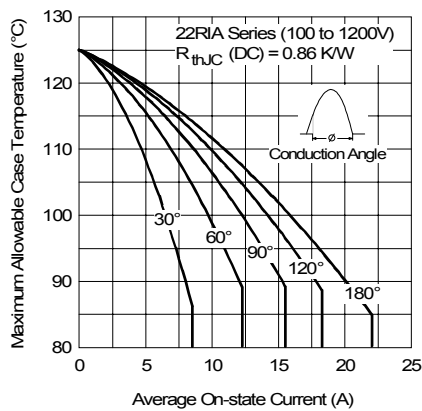
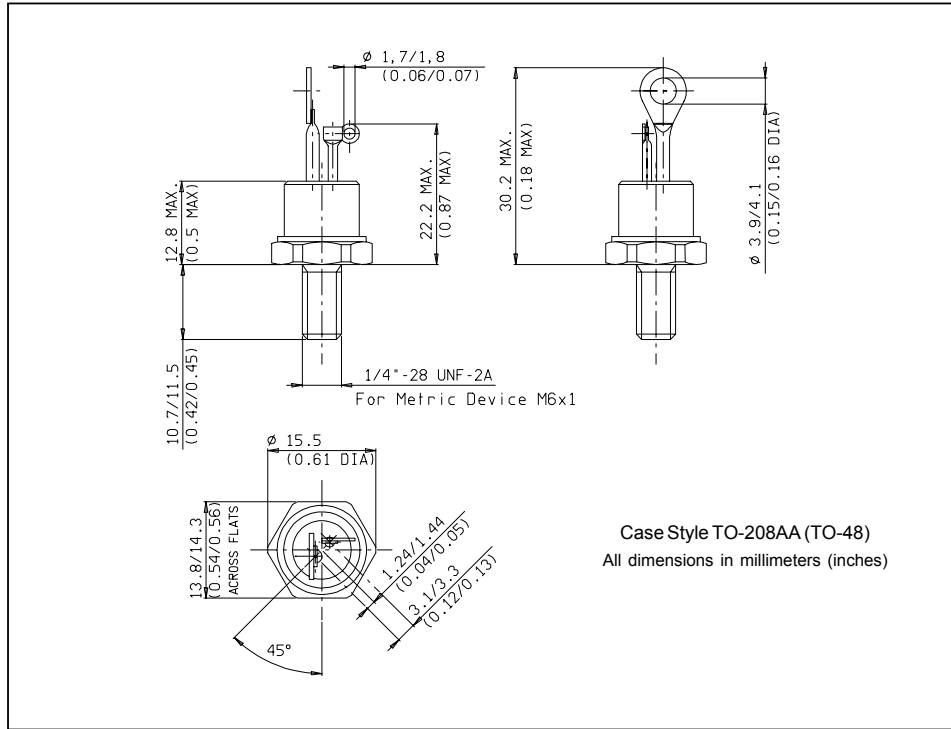


Fig. 1 - Current Ratings Characteristic

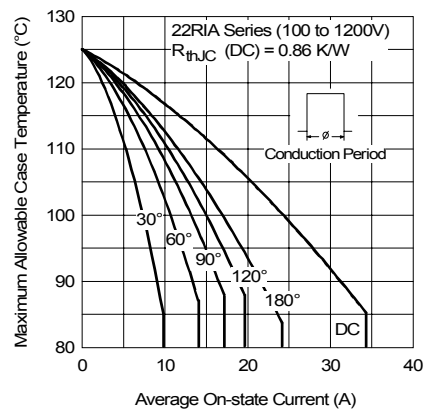


Fig. 2 - Current Ratings Characteristic

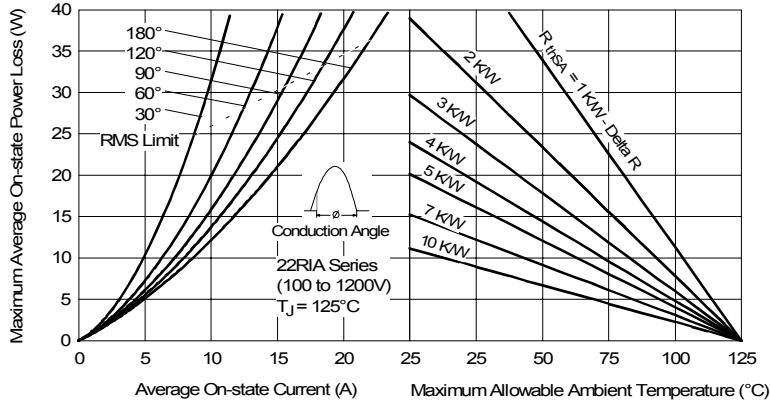


Fig. 3 - On-state Power Loss Characteristics

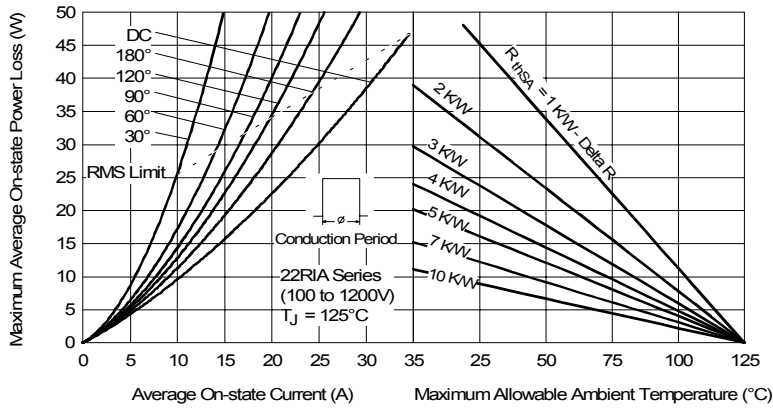


Fig. 4 - On-state Power Loss Characteristics

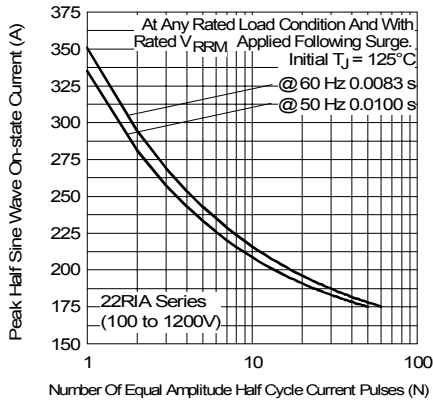


Fig. 5 - Maximum Non-Repetitive Surge Current

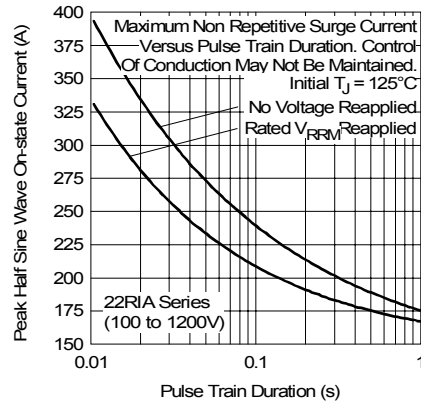


Fig. 6 - Maximum Non-Repetitive Surge Current

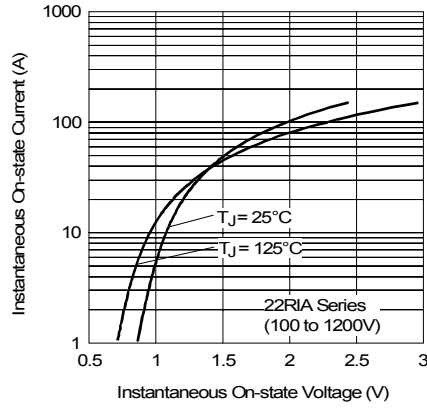


Fig. 7 - Forward Voltage Drop Characteristics

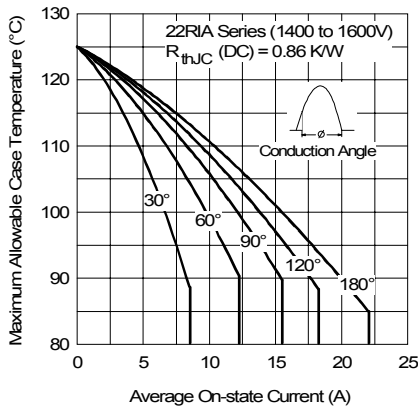


Fig. 8 - Current Ratings Characteristics

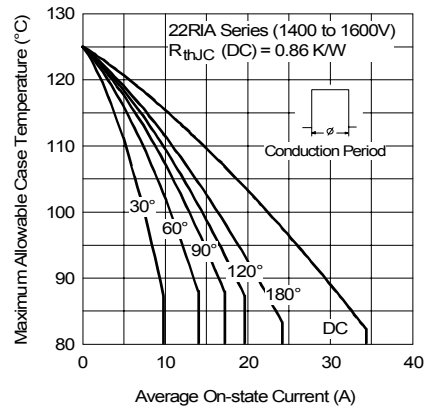


Fig. 9 - Current Ratings Characteristics

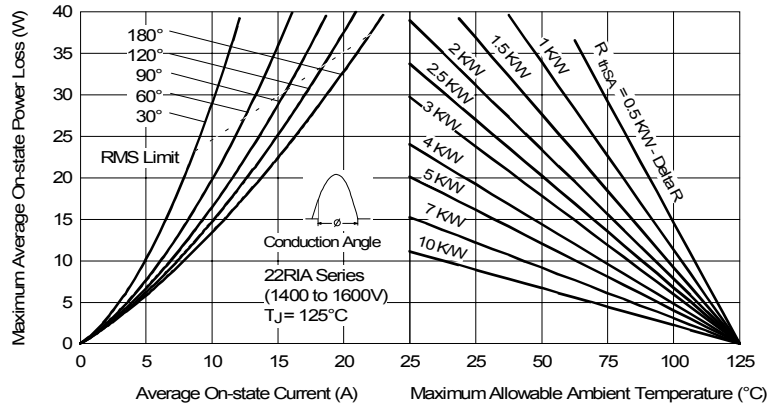


Fig. 10 - On-state Power Loss Characteristics

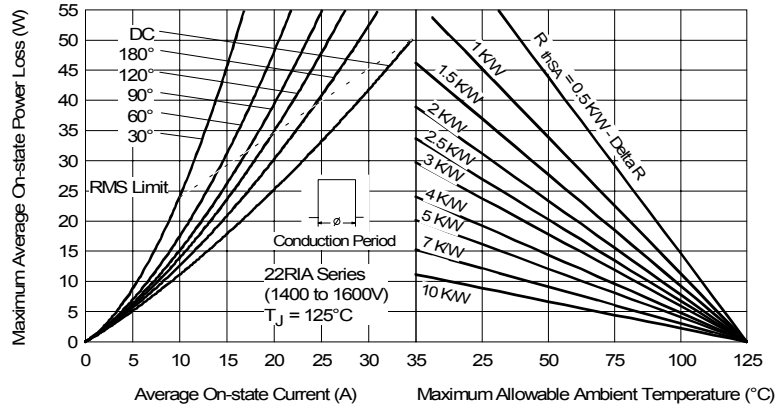


Fig. 11 - On-state Power Loss Characteristics

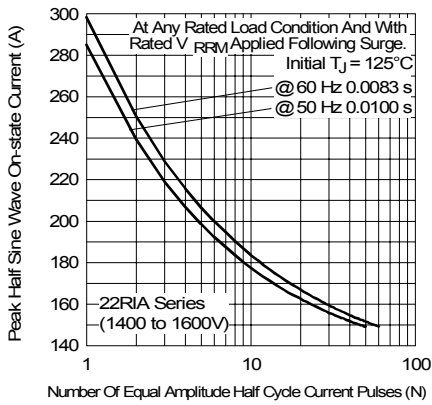


Fig. 12 - Maximum Non-Repetitive Surge Current

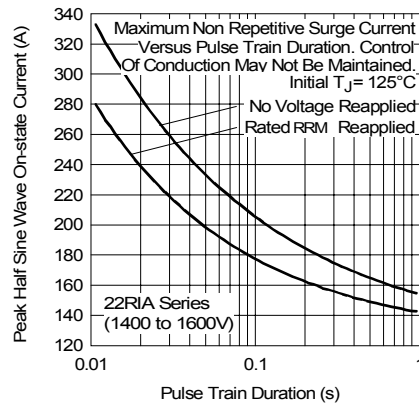


Fig. 13 - Maximum Non-Repetitive Surge Current

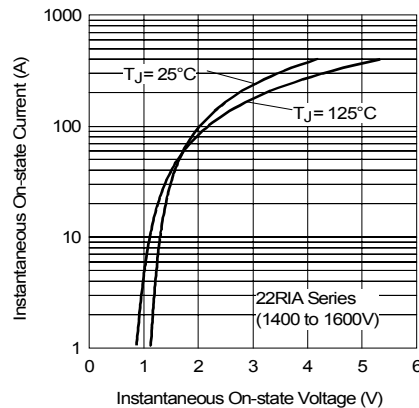


Fig. 14 - Forward Voltage Drop Characteristics

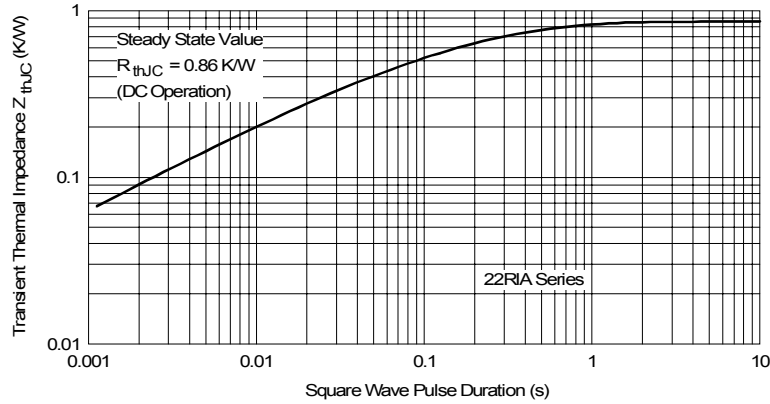


Fig. 15 - Thermal Impedance Z_{thJC} Characteristics

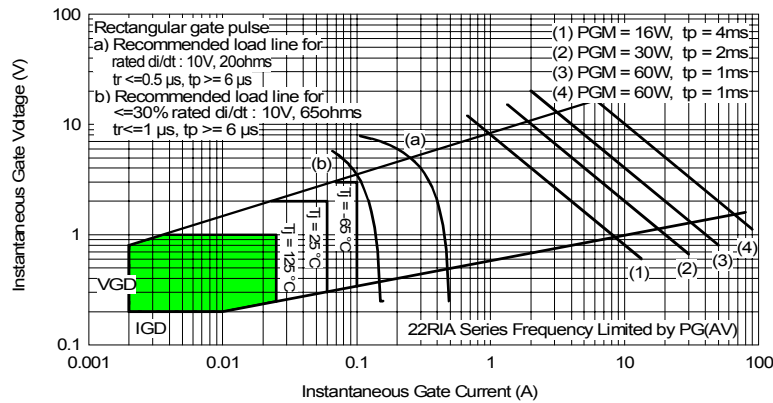


Fig. 16 - Gate Characteristics

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 U.S.A. Tel: (310) 322 3331. Fax: (310) 322 3332.
EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, U.K. Tel: ++ 44 1883 732020. Fax: ++ 44 1883 733408.
IR CANADA: 15 Lincoln Court, Brampton, Markham, Ontario L6T3Z2. Tel: (905) 453 2200. Fax: (905) 475 8801.
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg. Tel: ++ 49 6172 96590. Fax: ++ 49 6172 965933.
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino. Tel: ++ 39 11 4510111. Fax: ++ 39 11 4510220.
IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo, Japan 171. Tel: 81 3 3983 0086.
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994. Tel: ++ 65 838 4630.
IR TAIWAN: 16 Fl. Suite D.207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan. Tel: 886 2 2377 9936.